TM50N06Y

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

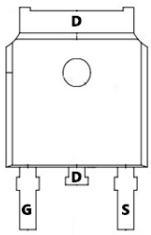
General Features

V_{DS} = 60V I_D =50A

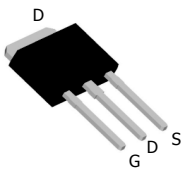
$R_{DS(ON)}$=12 mΩ (typ.)@ V_{GS}=10V

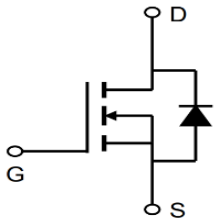
100% UIS Tested
100% R_g Tested

Green Product



Y:TO-251-3L





Marking: 50N06

Absolute Maximum Ratings (T_A= 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain CurrentT_C=25℃	50	A
	Continuous Drain CurrentT_C=100℃	32	
I_{DM}	Pulsed Drain Current[3]	185	
P_D	Power Dissipation	62.5	W
E_{AS}	Single pulse avalanche energy[1]	98	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristic

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	2	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	62	℃/W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=60V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	1.2	1.8	2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance	V_{GS}=10V,I_D=20A	---	12	17	mΩ
		V_{GS}=4.5V,I_D=20A	---	16	23	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=30V, V_{GS}=0V, f=1MHz	---	1798	---	pF
C_{oss}	Output Capacitance		---	112	--	
C_{rss}	Reverse Transfer Capacitance		---	91	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=30V, I_D=20A, R_{ENG}=3Ω,V_{GS}=10V	---	12	---	ns
t_r	Rise Time		---	24	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	59	---	ns
t_f	Fall Time		---	8	---	ns
Q_{gs}	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=20A	---	39	---	nc
Q_{gd}	Gate-Source Charge		---	7.7	---	nc
Q_g	Gate-Drain “Miller” Charge		---	8.2	---	nc
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=20A	---	---	1.2	V
I_S	Continuous Drain Curren	VD=VG=0V	---	---	50	A
I_{SM}	Pulsed Drain Current		---	---	185	A
Trr	Reverse Recovery Time[3]	I_F=20A,T_J=25℃	---	29	---	ns
Qrr	Reverse Recovery Charge	dI/dt=100A/us	---	21	---	nc

Notes:
1.L=0.5mH, V_{DD}=30V, Start T_J=25℃.
2.Limited by maximum junction temperature.
3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Performance Characteristics

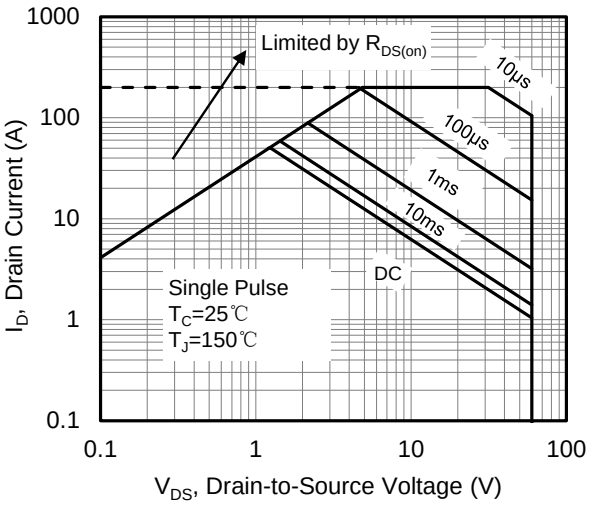


Figure 1. Maximum Safe Operating Area

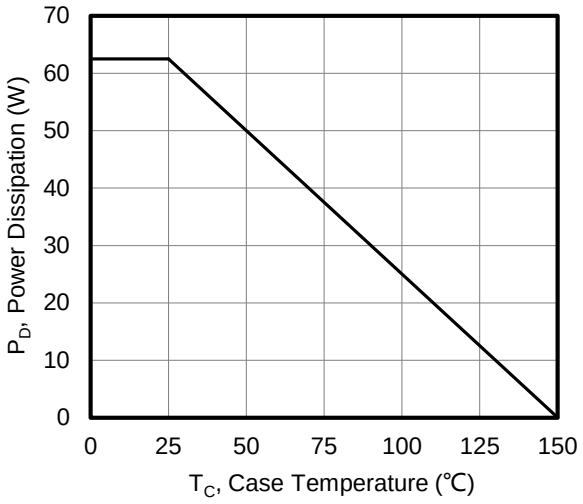


Figure 2. Maximum Power Dissipation vs Case Temperature

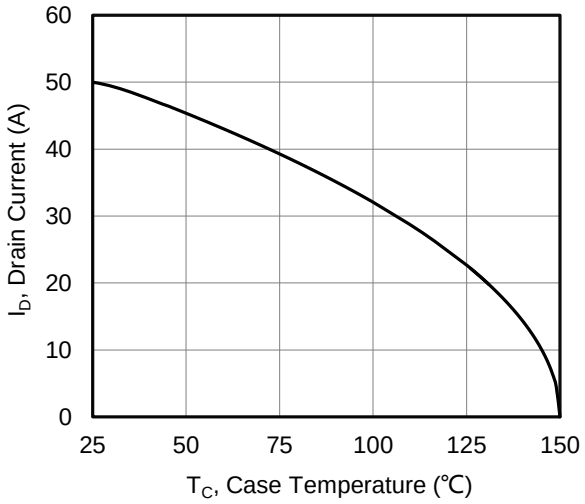


Figure 3. Maximum Continuous Drain Current vs Case Temperature

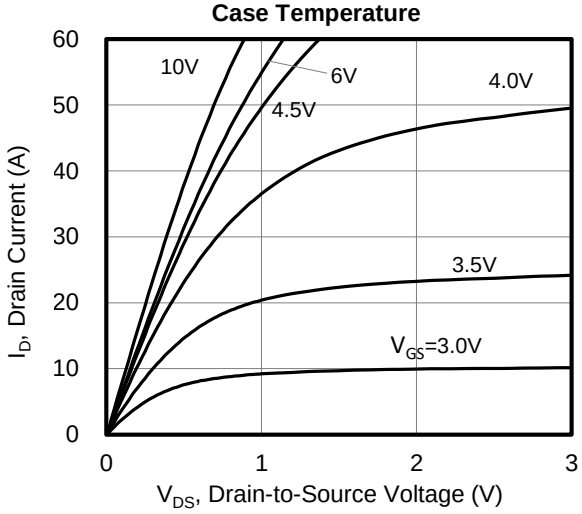
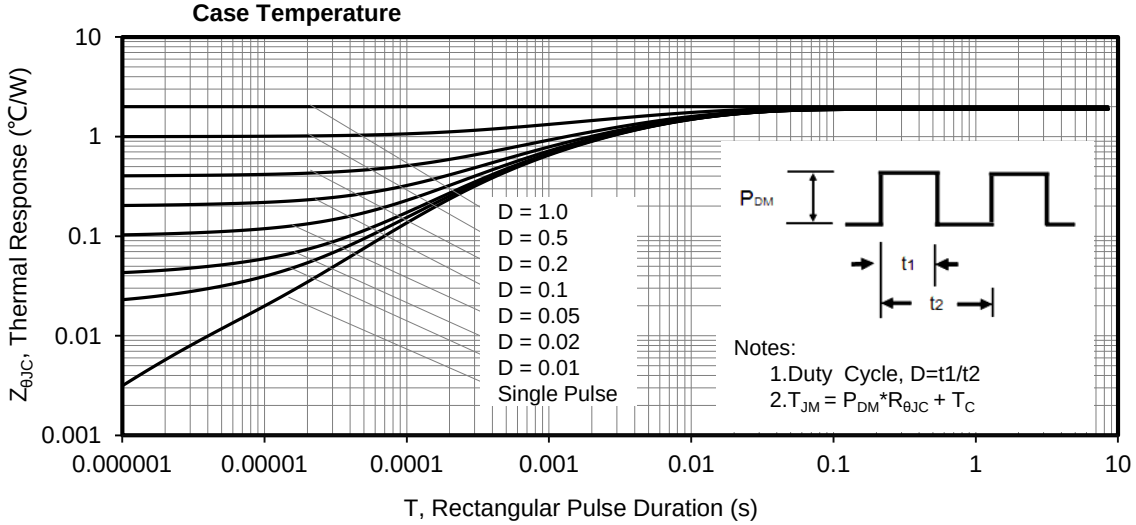


Figure 4. Typical output Characteristics



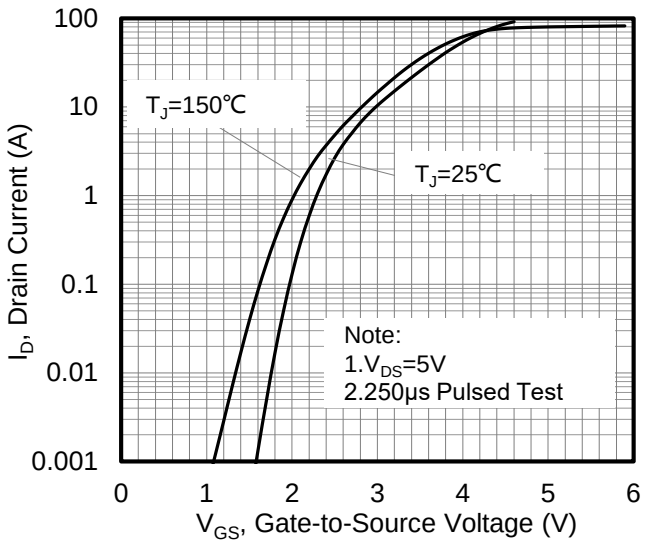


Figure 6. Typical Transfer Characteristics

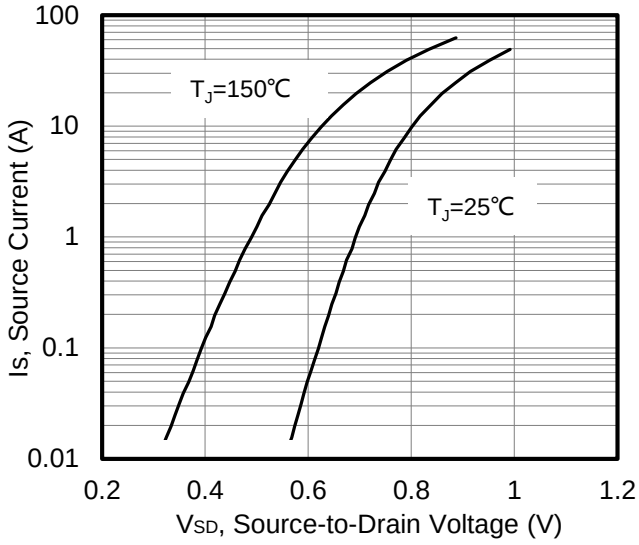


Figure 7. Typical Body Diode Transfer Characteristics

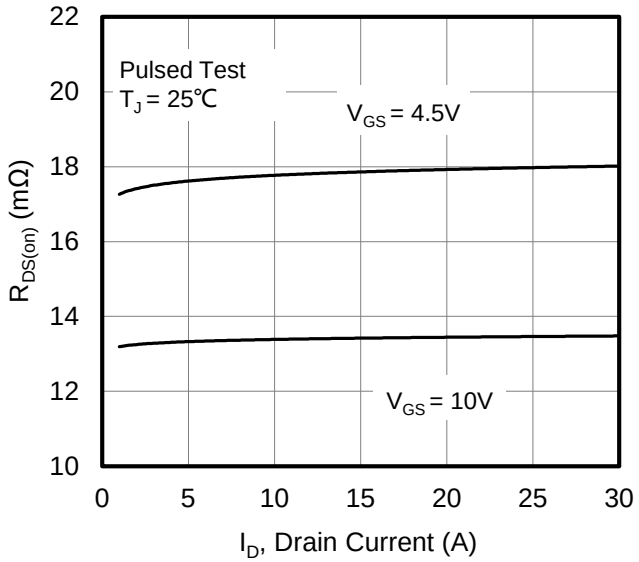


Figure 8. Drain-to-Source On Resistance vs Drain Current

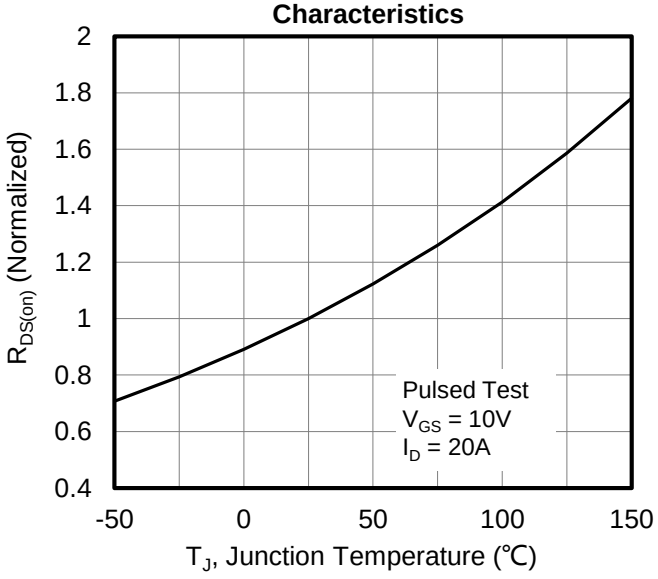


Figure 9. Normalized On Resistance vs Junction Temperature

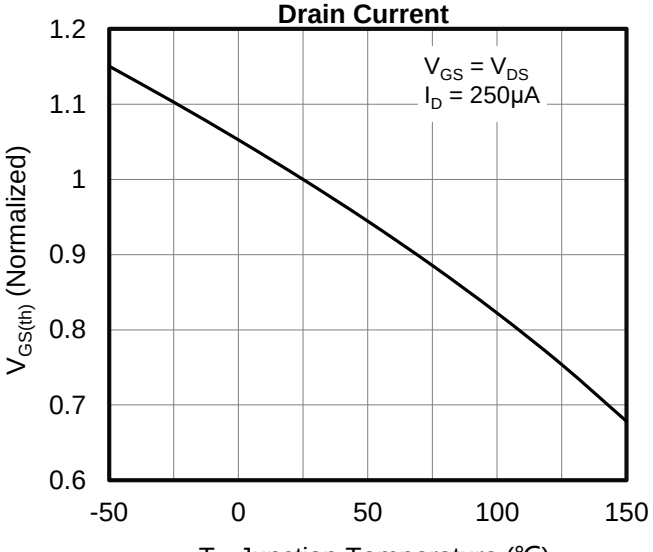


Figure 10. Normalized Threshold Voltage vs Junction Temperature

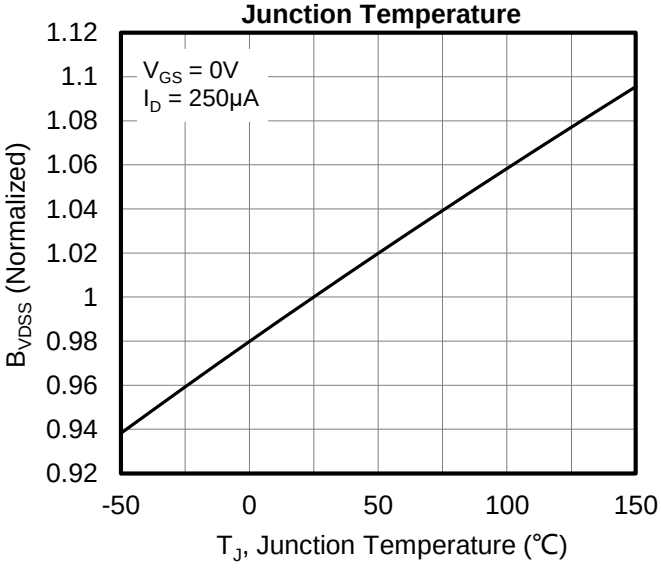


Figure 11. Normalized Breakdown Voltage vs Junction Temperature

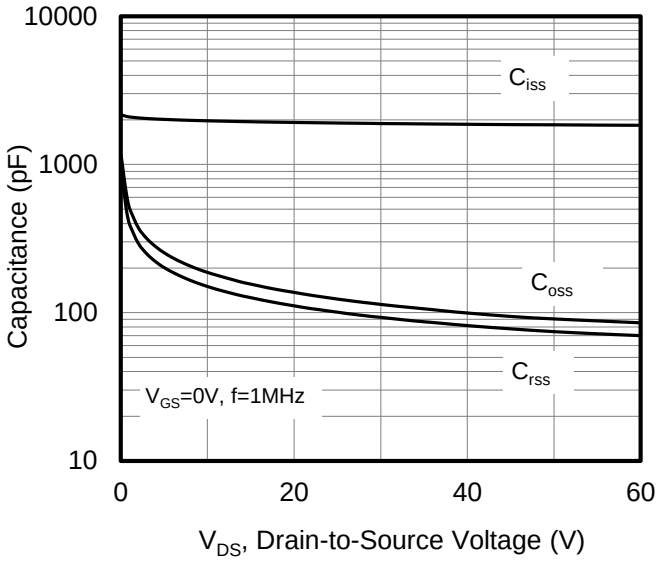


Figure 12. Capacitance Characteristics

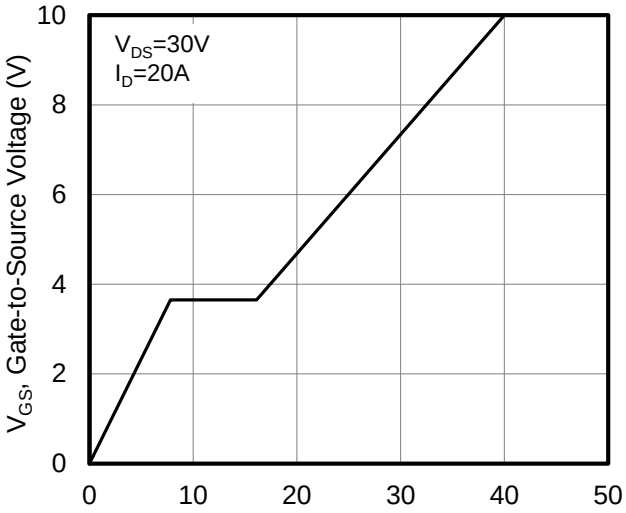
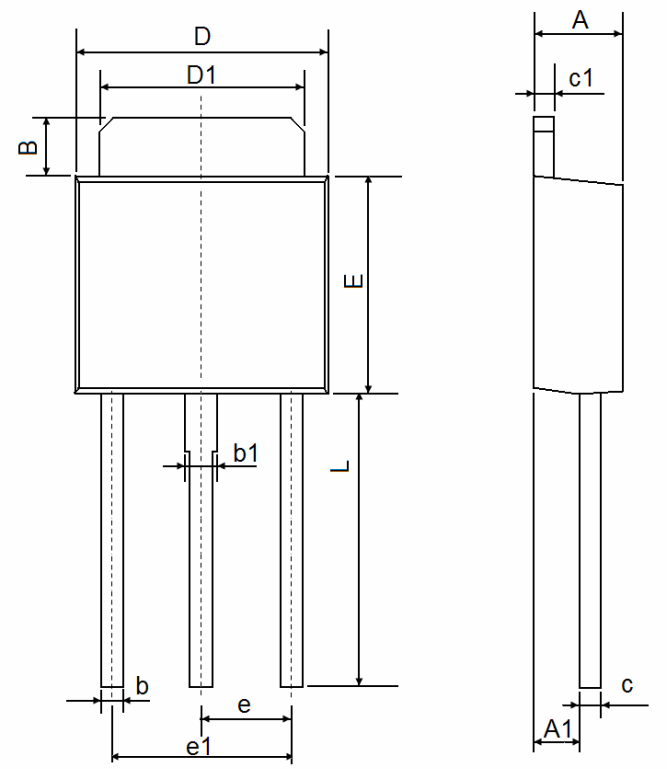


Figure 13. Typical Gate Charge vs Gate to Source Voltage

Package Information:TO-251-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311